Amendments to the Claims:

The following listing of claims replaces all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (original) A semiconductor device which has a synthetic high-molecular compound, with which a semiconductor element and at least part of electrical connecting means used for electrically connecting the semiconductor device to external devices are covered, in which

the synthetic high-molecular compound contains a compound having a three-dimensional steric structure which is formed by linking plural third organosilicon polymers, each of which has a molecular weight of 2×10^4 to 8×10^5 and which have been formed by linking at least one first organosilicon polymers having a crosslinked structure using siloxane (Si-O-Si combination) with at least one second organosilicon polymers having a linear linked structure using siloxane through siloxane bonds, with covalent bonds resulting from addition reaction.

2. (original) The semiconductor device as claimed in claim 1, in which the synthetic high-molecular compound contains a compound having a three-dimensional steric structure which is formed by linking plural third organosilicon polymers, each of which has a molecular weight of 2×10^4 to 8×10^5 and which have been formed by alternately and linearly linking a first organosilicon polymer having a crosslinked structure using siloxane with a second organosilicon polymer having a linear linked structure using siloxane through a siloxane bond, with covalent bonds resulting from addition reaction.

3. (original) The semiconductor device as claimed in claim 1, in which

the semiconductor element is either a SiC semiconductor element using a wide gap semiconductor or a GaN semiconductor element using a wide gap semiconductor,

the first organosilicon polymer is at least one selected from the group consisting of polyphenylsilsesquioxane, polymethylsilsesquioxane, polyethylsilsesquioxane, and polypropylsilsesquioxane, and

the second organosilicon polymer is at least one selected from the group consisting of polydimethylsiloxane, polydiethylsiloxane, polydiphenylsiloxane, and polymethylphenylsiloxane.

4. (original) The semiconductor device as claimed in claim 1, in which

the semiconductor element is a wide gap semiconductor light-receiving element, a wide gap semiconductor light-emitting element, or a combination thereof,

the first organosilicon polymer is at least one selected from the group consisting of polyphenylsilsesquioxane, polymethylsilsesquioxane, polyethylsilsesquioxane, and polypropylsilsesquioxane, and

the second organosilicon polymer is at least one selected from the group consisting of polydimethylsiloxane, polydiethylsiloxane, polydiphenylsiloxane, and polymethylphenylsiloxane.

5-8. (canceled)

9. (previously presented) The semiconductor device as claimed in claim 1, in which the molecular weight of the first organosilicon polymer is lower than that of the second organosilicon polymer.

10. (canceled)

11. (previously presented) The semiconductor device as claimed in claim 2, in which the molecular weight of the first organosilicon polymer is lower than that of the second organosilicon polymer.

12. (previously presented) The semiconductor device as claimed in claim 3, in which the molecular weight of the first organosilicon polymer is lower than that of the second organosilicon polymer.

13. (previously presented) The semiconductor device as claimed in 4, in which the molecular weight of the first organosilicon polymer is lower than that of the second organosilicon polymer.

14-15. (canceled)